Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-163003	Application No. 09/898,986
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Yamazaki, et al.	
		Filing Date July 3, 2001	Group Art Unit 2813

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	5,898,204	4/1999	Watanabe			
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	AI						

Foreign Patent Documents or Published Foreign Patent Applications

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	AJ	04-206971	07/28/92	JAPAN				
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Examiner Initial	Desig. ID	Document
	AP	Wang et al., Enhanced Performance of Accumulation Mode 0.5 μm CMOS/SOI Operated at 300 K and 85 K, IEEE, IEDM 91, pp. 679-682.
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Examiner Signature	Date Considered
Hoa Pham	10/28/03

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